Abstracts

Laser-Activated p-i-n Diode Switch for RF Application (Short Papers)

A. Rosen, P. Stabile, W. Janton, A. Gombar, P. Basile, J. Delmaster and R. Hurwitz. "Laser-Activated p-i-n Diode Switch for RF Application (Short Papers)." 1989 Transactions on Microwave Theory and Techniques 37.8 (Aug. 1989 [T-MTT]): 1255-1257.

There is a growing interest in optically controlled high-power switches from HF to millimeter wave. This paper deals specifically with the results obtained utilizing an optically activated RF switch in the 2-30 MHz range. Preliminary testing of a 0.25-mm-thick p-i-n device activated with 116 W peak optical power from a two-dimensional laser array in a 50 Omega system has yielded isolation between 20.8 and 49 dB, and an average insertion loss of. 0.38 dB when measured between 2.5 and 30 MHz.

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